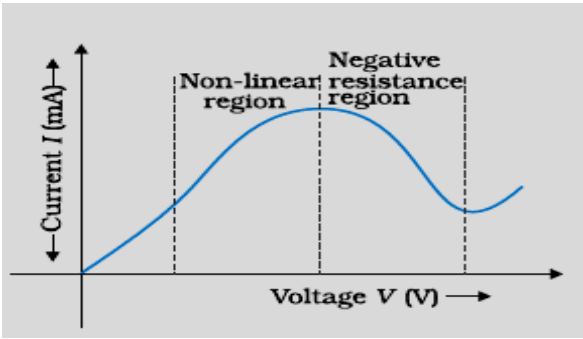


Strictly Confidential (For Internal and Restricted Use only)
Senior School Certificate Examination
Marking Scheme - Physics (Code 55/1/3)

1. The marking scheme provides general guidelines to reduce subjectivity in the marking. The answers given in the marking scheme are suggested answers. The content is thus indicated. If a student has given any other answer, which is different from the one given in the marking scheme, but conveys the meaning correctly, such answers should be given full weightage.
2. In value based questions, any other individual response with suitable justification should also be accepted even if there is no reference to the text.
3. Evaluation is to be done as per instructions provided in the marking scheme. It should not be done according to one's own interpretation or any other consideration. Marking scheme should be adhered to and religiously followed.
4. If a question has parts, please award in the right hand side for each part. Marks awarded for different part of the question should then be totaled up and written in the left hand margin and circled.
5. If a question does not have any parts, marks are to be awarded in the left hand margin only.
6. If a candidate has attempted an extra question, marks obtained in the question attempted first should be retained and the other answer should be scored out.
7. No marks are to be deducted for the cumulative effect of an error. The student should be penalized only once.
8. Deduct $\frac{1}{2}$ mark for writing wrong units, missing units, in the final answer to numerical problems.
9. Formula can be taken as implied from the calculations even if not explicitly written.
10. In short answer type question, asking for two features / characteristics / properties if a candidate writes three features, characteristics / properties or more, only the correct two should be evaluated.
11. Full marks should be awarded to a candidate if his / her answer in a numerical problem is close to the value given in the scheme.
12. In compliance to the judgement of the Hon'ble Supreme Court of India, Board has decided to provide photocopy of the answer book(s) to the candidates who will apply for it along with the requisite fee from 2012 examination. Therefore, it is all the more important that the evaluation is done strictly as per the value points given in the marking scheme so that the Board could be in a position to defend the evaluation at any forum.
13. The Examiner shall also have to certify in the answer book that they have evaluated the answer book strictly in accordance with the value points given in the marking scheme and correct set of question paper.
14. Every Examiner shall also ensure that all the answers are evaluated, marks carried over to the title paper, correctly totaled and written in figures and words.
15. In the past it has been observed that the following are the common types of errors committed by the Examiners
 - Leaving answer or part thereof unassessed in an answer script.
 - Giving more marks for an answer than assigned to it or deviation from the marking scheme.
 - Wrong transference of marks from the inside pages of the answer book to the title page.
 - Wrong question wise totaling on the title page.
 - Wrong totaling of marks of the two columns on the title page.
 - Wrong grand total.
 - Marks in words and figures not tallying.
 - Wrong transference to marks from the answer book to award list.
 - Answer marked as correct (\checkmark) but marks not awarded.
 - Half or part of answer marked correct (\checkmark) and the rest as wrong (\times) but no marks awarded.
16. Any unassessed portion, non carrying over of marks to the title page or totaling error detected by the candidate shall damage the prestige of all the personnel engaged in the evaluation work as also of the Board. Hence in order to uphold the prestige of all concerned, it is again reiterated that the instructions be followed meticulously and judiciously.

MARKING SCHEME SET 55/1/3 (DELHI)

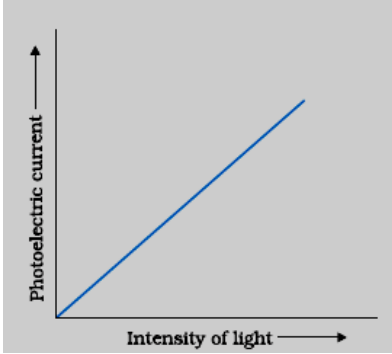
Q.No.	Expected Answer/Value Points	Marks	Total Marks
1.	Drift velocity v_d , is the directed velocity acquired by the electrons for a unit value of the applied Electric field. Current, $I = neAv_d$	½ ½	1
2.	Modulation index = $\frac{a_m}{a_c}$ $= \frac{1.5}{3.0} = 0.5$	½ ½	1
3.	$\vec{F} = q(\vec{v} \times \vec{B})$ Perpendicular to the plane formed by \vec{v} and \vec{B} / $\vec{F} \perp \vec{v}$ and $\vec{F} \perp \vec{B}$ [Note: Give full credit for writing the expression only.]	½ ½	1
4.		1	1
5.	20cm	1	1
6.	X: Channel It connects Transmitter and Receiver	½ ½	1
7.	Glass. In glass there is no electromagnetic induction, due to presence of Earth's magnetic field, unlike in the case of metallic ball.	½ ½	1
8.	If Electric field is not normal, it will have non-zero component along the surface. In that case, work would be done in moving a charge on an equipotential surface.	1	1
9.	<div style="border: 1px solid black; padding: 5px; display: inline-block; margin-bottom: 10px;"> Calculation of Potential energy of the dipole 2 </div> $\tau = pE \sin \theta$ $6\sqrt{3} = pE \sin 60^\circ = pE \times \frac{\sqrt{3}}{2}$ $\Rightarrow pE = 12$	½ ½	

	Potential energy $U = -pE \cos \theta$ $= -12 \times \cos 60^\circ = -6J$	$\frac{1}{2}$ $\frac{1}{2}$	2						
10.	<table border="1"> <tr> <td>Underlying principle</td> <td>1</td> </tr> <tr> <td>Brief working</td> <td>1</td> </tr> </table> <p>It makes use of the principle that the energy of the charged particles / ions can be made to increase in presence of crossed Electric and magnetic fields.</p> <p>A normal Magnetic field acts on the charged particle and makes them move in a circular path .While moving from one dee to another; particle is acted upon by the alternating electric field, and is accelerated by this field, which increases the energy of the particle.</p>	Underlying principle	1	Brief working	1	1 1	2		
Underlying principle	1								
Brief working	1								
11.	<table border="1"> <tr> <td>Effect on glow of bulb in</td> <td>Part (i)</td> <td>1</td> </tr> <tr> <td></td> <td>Part (ii)</td> <td>1</td> </tr> </table> <p>(i) Reactance of the capacitor will decrease, resulting in increase of the current in the circuit. Therefore the bulb will glow brighter.</p> <p>(ii) Increased resistance will decrease the current in the circuit, which will decrease glow of the bulb.</p> <p>[Note : Do not deduct any mark for not giving the reasons]</p>	Effect on glow of bulb in	Part (i)	1		Part (ii)	1	1 1	2
Effect on glow of bulb in	Part (i)	1							
	Part (ii)	1							
12.	<table border="1"> <tr> <td>Part (a) and its reason</td> <td>$\frac{1}{2} + \frac{1}{2}$</td> </tr> <tr> <td>Part (b) and its reason</td> <td>$\frac{1}{2} + \frac{1}{2}$</td> </tr> </table> <p>(a) deuteron $\lambda = \frac{h}{\sqrt{2mqV}}$ $\frac{\lambda_d}{\lambda_\alpha} = \sqrt{\frac{m_\alpha q_\alpha}{m_d q_d}} = \sqrt{\frac{2m_d \times 2q_d}{m_d q_d}} = \frac{2}{1}$ $\Rightarrow \lambda_d > \lambda_\alpha$</p> <p>(b) deuteron KE= qV $\therefore q_\alpha > q_d$, for the same accelerating potential, we have $(KE)_d > (KE)_\alpha$</p>	Part (a) and its reason	$\frac{1}{2} + \frac{1}{2}$	Part (b) and its reason	$\frac{1}{2} + \frac{1}{2}$	$\frac{1}{2}$ $\frac{1}{2}$ $\frac{1}{2}$	2		
Part (a) and its reason	$\frac{1}{2} + \frac{1}{2}$								
Part (b) and its reason	$\frac{1}{2} + \frac{1}{2}$								

13.	<table border="1" style="width: 100%;"> <tr> <td style="width: 80%;">Identification of magnetic material</td> <td style="width: 20%; text-align: right;">½ + ½</td> </tr> <tr> <td>Susceptibility</td> <td style="text-align: right;">½ + ½</td> </tr> </table> <p>A: Paramagnetic B: Diamagnetic</p> <p>Susceptibility For A: positive For B: negative</p>	Identification of magnetic material	½ + ½	Susceptibility	½ + ½	½ ½ ½ ½	2
Identification of magnetic material	½ + ½						
Susceptibility	½ + ½						
14.	<table border="1" style="width: 100%;"> <tr> <td style="width: 80%;">Statements of two Laws</td> <td style="width: 20%; text-align: right;">½ + ½</td> </tr> <tr> <td>Justification</td> <td style="text-align: right;">½ + ½</td> </tr> </table> <p>Junction rule: At any junction, the sum of the currents entering the junction is equal to the sum of currents leaving the junction.</p> <p>Alternatively, $\sum i = 0$</p> <p>Justification : Conservation of charge</p> <p>Loop rule: The Algebraic sum of changes in the potential around any closed loop involving resistors and cells in the loop is zero.</p> <p>Alternatively, $\sum \Delta V = 0$, where ΔV is the changes in potential</p> <p>Justification : Conservation of energy</p>	Statements of two Laws	½ + ½	Justification	½ + ½	½ ½ ½ ½	2
Statements of two Laws	½ + ½						
Justification	½ + ½						
15.	<table border="1" style="width: 100%;"> <tr> <td style="width: 80%;">Finding flux in two cases</td> <td style="width: 20%; text-align: right;">1+1</td> </tr> </table> <p>$\phi = EA \cos \theta$ $= 4 \times 10^3 \times 25 \times 10^{-4} \cos 0$ $= 10 \text{ Nm}^2 \text{ C}^{-1}$</p> <p>$\phi = 4 \times 10^3 \times 25 \times 10^{-4} \cos 60$ $= 5 \text{ Nm}^2 \text{ C}^{-1}$</p>	Finding flux in two cases	1+1	½ ½ ½ ½	2		
Finding flux in two cases	1+1						
16.	<table border="1" style="width: 100%;"> <tr> <td style="width: 80%;">(a) Estimation of number of photons per second</td> <td style="width: 20%; text-align: right;">1</td> </tr> <tr> <td>(b) plot showing the variation</td> <td style="text-align: right;">1</td> </tr> </table> <p>(a) power = $n h \nu$, where n = no. of photons per second</p> $n = \frac{N}{t} = \frac{3.0 \times 10^{-3}}{6.6 \times 10^{-34} \times 5 \times 10^{14}}$ <p style="text-align: center;"> $= .0909 \times 10^{17}$ photons/second $= 9.1 \times 10^{15}$ photons/second </p>	(a) Estimation of number of photons per second	1	(b) plot showing the variation	1	½ ½	
(a) Estimation of number of photons per second	1						
(b) plot showing the variation	1						

[Note: Even if the student doesn't write the formula and calculates correctly, give full credit to this part]

(b)



1

2

17.

Truth Table	1
Names of gates used	$\frac{1}{2} + \frac{1}{2}$

Truth Table

Input		Output	
A	B	Y'	Y
0	0	0	0
0	1	1	0
1	0	1	1
1	1	1	1

Gate R: OR Gate
S: AND Gate

OR

Identification	1
Truth Table	1

P: NAND Gate
Q: OR Gate

Truth Table

Input		Output
A	B	X
0	0	1
1	0	1
0	1	1
1	1	1

1

$\frac{1}{2}$
 $\frac{1}{2}$

2

$\frac{1}{2}$
 $\frac{1}{2}$

1

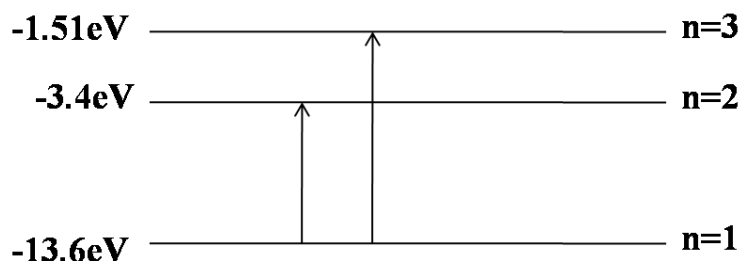
2

18.	<div style="border: 1px solid black; padding: 5px; margin-bottom: 10px;"> Explanation of the given statement 1 + 1 </div> <p>In the first case, the overlapping of the contributions of the wavelets from two halves of a single slit produces a minimum because corresponding wavelets from two halves have a path difference of $\frac{\lambda}{2}$.</p> <p>In the second case, the overlapping of the wavefronts from the two slits produces first maximum because these wavefronts have the path difference of λ.</p> <p>(Alternatively, if a student writes the conditions given below, give full credit.)</p> <p>Condition for first minimum in single slit diffraction is , $\theta \approx \lambda / a$, Whereas in case of two narrow slits separated by distance a, first maximum occurs at angle $\theta \approx \lambda / a$</p> <p>[Note: Award 1 mark even if the candidate attempts this question partly.]</p>	1 1	2
19.	<div style="border: 1px solid black; padding: 5px; margin-bottom: 10px;"> (a) Statement of Ampere’s circuital Law 1 ½ (b) Calculation of net magnetic field (i) inside and (ii) outside 1 ½ </div> <p>(a) Statement of law Expression of the law in integral form: $\oint \vec{B} \cdot d\vec{l} = \mu_0 i$</p> <p>(Award 1 mark if the student just writes the integral form of Ampere’s circuital law)</p> <p>(b) $B = \mu_0 n I$</p> <p>Magnitude of net magnetic field inside the combined system on the axis , $B = B_1 - B_2$ $\Rightarrow B = \mu_0 (n_1 - n_2) I$</p> <p>Also accept if the student writes $B = \mu_0 (n_2 - n_1) I$</p> <p>(iii) Outside the combined system, the net magnetic field is zero.</p>	1 ½ ½ ½	3
20.	<div style="border: 1px solid black; padding: 5px; margin-bottom: 10px;"> Finding maximum energy level of hydrogen atoms ½ Calculation of wavelengths 2 ½ </div> $E_n = \frac{-13.6}{n^2} eV$ <p>Energy required to excite hydrogen atoms from ground state to the second state $= E_{\text{final}} - E_{\text{initial}}$ $= -1.51 - (-13.6) eV = 12.09 eV$</p>	½	

i.e. Hydrogen atoms would be excited upto third energy level(i.e. n=3)/ second excited state.

[**Note :** If the student just writes gaseous hydrogen is made up of the molecule, or just writes the formula for E_n ,award this ½ mark.]

Alternatively:



For Lyman series

$$\frac{1}{\lambda} = R \left[\frac{1}{n_f^2} - \frac{1}{n_i^2} \right]$$

$$\frac{1}{\lambda} = 1.097 \times 10^7 \left[\frac{1}{1} - \frac{1}{9} \right]$$

$$\lambda = \frac{9}{8 \times 1.097 \times 10^7} = 1.025 \times 10^{-7}$$

$$= 102.5 \text{ nm}$$

For Balmer series

$$\frac{1}{\lambda} = 1.097 \times 10^7 \left[\frac{1}{4} - \frac{1}{16} \right]$$

$$\lambda = \frac{16}{3 \times 1.097 \times 10^7}$$

$$= 4.86 \times 10^{-7}$$

$$= 486 \text{ nm}$$

[**Note:** Also accept the answers given in terms of R only]

½

½

½

½

½

3

21.

(a) Derivation of the expression of energy stored per unit volume	2
(b) Calculation of work done	1

(a) Work done by the source of potential, in storing an additional charge (dq) , is

$$dW = V.dq$$

But $V = q / C$

$$\Rightarrow dW = \frac{q}{C} dq$$

Total work done in storing the charge Q,

½

$$\int dW = \int_0^Q \frac{q}{C} dq$$

$$W = \frac{1}{C} \left(\frac{q^2}{2} \right)_0^Q = \frac{Q^2}{2C}$$

This work is stored as electrostatic energy in the capacitor.

$$\because Q = CV, \quad \therefore U = \frac{1}{2} CV^2$$

$$\text{Energy stored per unit volume} = \frac{\frac{1}{2} CV^2}{Ad} = \frac{\frac{1}{2} \left(\frac{\epsilon_0 A}{d} \right) (Ed)^2}{Ad}$$

$$= \frac{1}{2} \epsilon_0 E^2$$

(b) Work done in moving the charge q from a to b, and from c to d is zero because Electric field is perpendicular to the displacement.

Work done from b to c = - Workdone from d to a

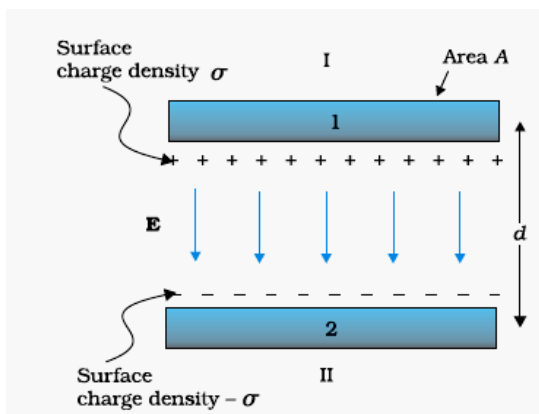
\therefore Total work done in moving a charge q over a closed loop = 0

(Award this one mark if a student writes correct answer directly)

OR

(a) Derivation of capacitance of parallel plate capacitor	2
(b) Finding the Ratio of surface charge densities	1

(a)



$$\text{Electric field between the plates of capacitor } E = \frac{\sigma}{\epsilon_0} = \frac{Q}{A\epsilon_0}$$

\therefore potential difference

$$V = Ed = \frac{Qd}{A\epsilon_0}$$

1/2

1/2

1/2

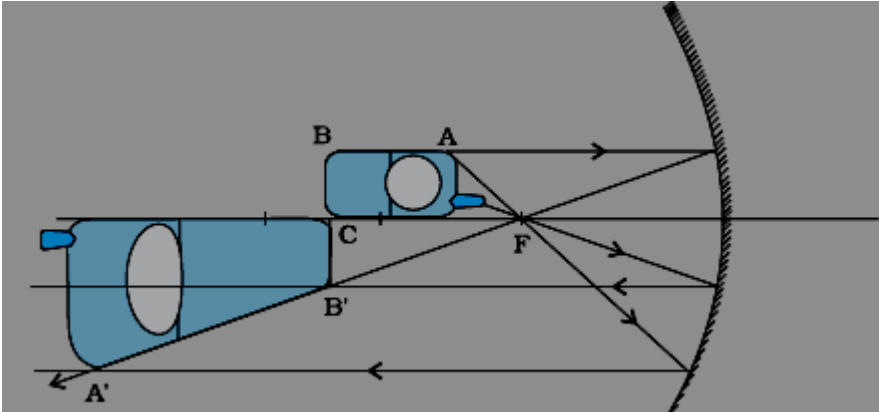
1/2

1/2

3

1/2

1/2

	<p>Capacitance</p> $C = \frac{Q}{V} = \frac{\epsilon_0 A}{d}$ <p>(b) When the two charged spherical conductors are connected by a conducting wire, they acquire the same potential</p> <p>i.e. $\frac{Kq_1}{R_1} = \frac{Kq_2}{R_2} \Rightarrow \frac{q_1}{R_1} = \frac{q_2}{R_2}$</p> <p>Hence, ratio of surface charge densities</p> $\frac{\sigma_1}{\sigma_2} = \frac{q_1/4\pi R_1^2}{q_2/4\pi R_2^2}$ $= \frac{q_1 R_2^2}{q_2 R_1^2}$ $= \frac{R_1}{R_2} \times \frac{R_2^2}{R_1^2} = \frac{R_2}{R_1}$	<p>1</p> <p>½</p> <p>½</p>	<p>3</p>				
<p>22.</p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="padding: 5px;">(a) Explanation with the help of suitable diagram</td> <td style="text-align: right; padding: 5px;">2</td> </tr> <tr> <td style="padding: 5px;">(b) Effect of covering of lower half of the mirror</td> <td style="text-align: right; padding: 5px;">1</td> </tr> </table> <p>(a)</p>  <p>Magnification is non-uniform because the position of the image of different parts of the phone, depends on their location with respect to the mirror. From the figure it can be observed that whereas $BC = B'C$, the images of the other parts of the phone, are getting magnified in accordance with their 'object distance' from the mirror.</p> <p>(b) By covering the mirror with an opaque material, the area of the reflecting surface has been reduced (i.e. halved). Therefore, the intensity of the image is reduced to half. (Award full marks even if student writes that there would be no effect on the size and / or position of the image.)</p>	(a) Explanation with the help of suitable diagram	2	(b) Effect of covering of lower half of the mirror	1	<p>1</p> <p>1</p> <p>1</p>	<p>3</p>
(a) Explanation with the help of suitable diagram	2						
(b) Effect of covering of lower half of the mirror	1						

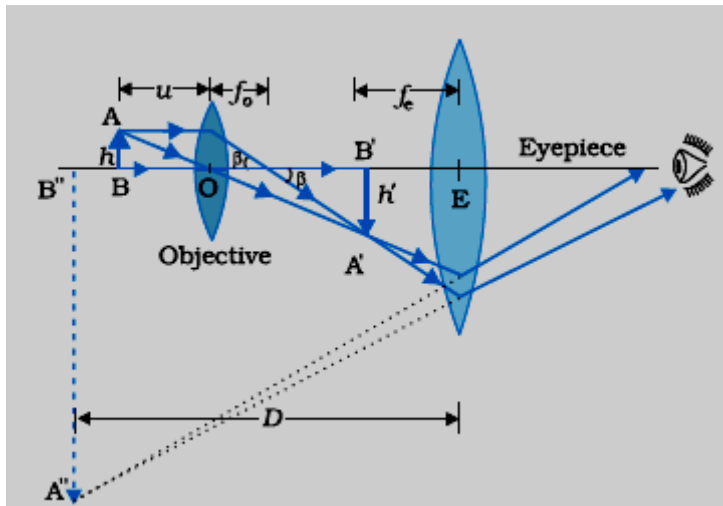
23.

Ray diagram of compound microscope

1 ½

Calculation of focal length of objective and eyepiece

1 ½



1½

For eyepiece $m_e = \frac{v_e}{u_e}$

$$u_e = \frac{v_e}{m_e} = \frac{-20}{5} \text{ cm} = -4 \text{ cm}$$

½

Also, $\frac{1}{f_e} = \frac{1}{v_e} - \frac{1}{u_e}$

$$\frac{1}{f_e} = \frac{-1}{20} + \frac{1}{4}$$

$$f_e = 5 \text{ cm}$$

½

$$m = m_e \times m_o$$

$$-20 = 5 \times m_o \Rightarrow m_o = -4$$

Also $|v_o| + |u_e| = 14$

$$\Rightarrow v_o = (14 - 4) \text{ cm} = 10 \text{ cm}$$

$$m_o = 1 - \frac{v_o}{f_o} \Rightarrow -4 = 1 - \frac{10}{f_o}$$

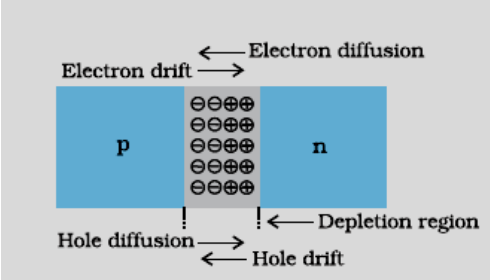
$$\Rightarrow f_o = 2 \text{ cm}$$

where subscripts e and o are used for eyepiece and objective respectively.

½

3

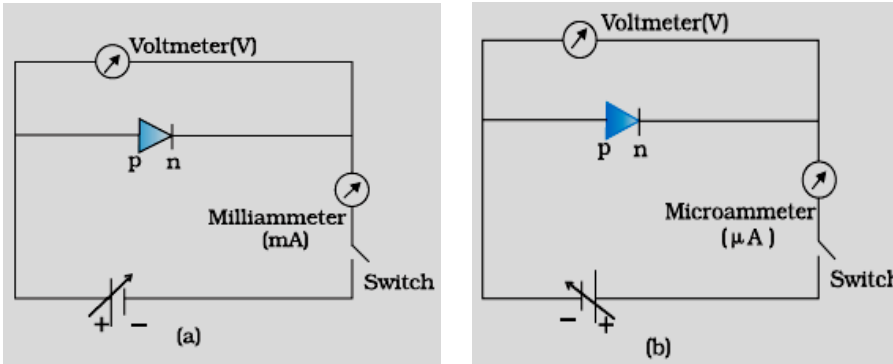
24.	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 80%;">Part (a)</td> <td style="width: 20%; text-align: center;">1</td> </tr> <tr> <td>Part (b)</td> <td style="text-align: center;">1</td> </tr> <tr> <td>Part (c)</td> <td style="text-align: center;">1</td> </tr> </table> <p>(a) γ - rays Range: 10^{19} to 10^{23} Hz [Note :If the student correctly identifies the name of the em wave award full marks]</p> <p>(b) To protect the eyes from large amount of UV radiations produced by welding arcs.</p> <p>(c) Because water molecules present in the materials readily absorb the infra red rays get heated up.</p> <p>Application for heating purposes, green house effect, Remote Switches (Any one / any other correct application.)</p>	Part (a)	1	Part (b)	1	Part (c)	1	<p>$\frac{1}{2}$ $\frac{1}{2}$</p> <p>1</p> <p>$\frac{1}{2}$</p> <p>$\frac{1}{2}$</p>	3
Part (a)	1								
Part (b)	1								
Part (c)	1								
25.	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 80%;">Calculation of potential gradient</td> <td style="width: 20%; text-align: center;">2</td> </tr> <tr> <td>Determination of emf of primary cell</td> <td style="text-align: center;">1</td> </tr> </table> <p>Current flowing in the potentiometer</p> $I = \frac{V}{R + R'}$ $= \frac{8.0}{5+15} A = 0.4 A$ <p>Potential drop across the potentiometer wire $V=IR=0.4 \times 5 = 2.0$ V Potential Gradient</p> $K = \frac{V}{l} = \frac{2.0}{1.0} = 2.0V/m$ <p>Unknown emf $E = kl'$ $= 2.0 \times 0.6V$ $= 1.2 V$</p>	Calculation of potential gradient	2	Determination of emf of primary cell	1	<p>$\frac{1}{2}$</p> <p>$\frac{1}{2}$</p> <p>$\frac{1}{2}$</p> <p>$\frac{1}{2}$</p> <p>$\frac{1}{2}$</p>	3		
Calculation of potential gradient	2								
Determination of emf of primary cell	1								
26.	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 80%;">(a) Derivation of the law of Radioactive decay</td> <td style="width: 20%; text-align: center;">1 $\frac{1}{2}$</td> </tr> <tr> <td>(b) (i) Processes expressing β^+ decay</td> <td style="text-align: center;">$\frac{1}{2} + \frac{1}{2}$</td> </tr> <tr> <td>(ii) Identification as isotope / isobar</td> <td style="text-align: center;">$\frac{1}{2}$</td> </tr> </table> <p>(a) $\frac{dN}{dt} = -\lambda N$</p> $\int_{N_0}^N \frac{dN}{N} = \int_0^t -\lambda dt$	(a) Derivation of the law of Radioactive decay	1 $\frac{1}{2}$	(b) (i) Processes expressing β^+ decay	$\frac{1}{2} + \frac{1}{2}$	(ii) Identification as isotope / isobar	$\frac{1}{2}$	$\frac{1}{2}$	
(a) Derivation of the law of Radioactive decay	1 $\frac{1}{2}$								
(b) (i) Processes expressing β^+ decay	$\frac{1}{2} + \frac{1}{2}$								
(ii) Identification as isotope / isobar	$\frac{1}{2}$								

	$[\log_e N]_{N_0}^N = -\lambda[t]_0^t$ $\log_e \frac{N}{N_0} = -\lambda t$ $N = N_0 e^{-\lambda t}$ <p>(b)</p> <p>(i) ${}_{11}^{22}\text{Na} \rightarrow {}_{10}^{22}\text{Ne} + e^+ + \nu$ Also accept , if a student does not identify the product nucleus and writes as</p> ${}_{11}^{22}\text{Na} \rightarrow {}_{10}^{22}\text{X} + e^+ + \nu$ <p>Basic process $p \rightarrow n + e^+ + \nu$</p> <p>(ii) Isobar</p>	<p>1/2</p> <p>1/2</p> <p>1/2</p> <p>1/2</p> <p>1/2</p>	<p>3</p>								
<p>27.</p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="padding: 5px;">(i) Effect of em waves on health</td> <td style="text-align: right; padding: 5px;">1</td> </tr> <tr> <td style="padding: 5px;">(ii) Values displayed</td> <td style="text-align: right; padding: 5px;">1</td> </tr> <tr> <td style="padding: 5px;">(iii) Estimation of the range</td> <td style="text-align: right; padding: 5px;">1</td> </tr> </table> <p>(i) Electromagnetic radiations emitted by an antenna can cause</p> <p>(a) Cardiac problem</p> <p>(b) Cancer</p> <p>(c) Giddiness and headache</p> <p>(any one of the above / or any other effect on health)</p> <p>(ii) Scientific temperament, awareness (any one / any other correct value)</p> <p>(iii) Range = $\sqrt{2h_f R}$</p> $= \sqrt{2 \times 20 \times 6.4 \times 10^6} \text{ km}$ $= \sqrt{4 \times 64 \times 10^6} = 16 \text{ km}$	(i) Effect of em waves on health	1	(ii) Values displayed	1	(iii) Estimation of the range	1	<p>1</p> <p>1</p> <p>1/2</p> <p>1/2</p>	<p>3</p>		
(i) Effect of em waves on health	1										
(ii) Values displayed	1										
(iii) Estimation of the range	1										
<p>28.</p>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="padding: 5px;">(a) Processes involved in the formation of depletion region</td> <td style="text-align: right; padding: 5px;">2</td> </tr> <tr> <td style="padding: 5px;">(b) Circuit diagrams</td> <td style="text-align: right; padding: 5px;">1/2 + 1/2</td> </tr> <tr> <td style="padding: 5px;">V-I characteristics in forward biasing and reverse biasing</td> <td style="text-align: right; padding: 5px;">1/2 + 1/2</td> </tr> <tr> <td style="padding: 5px;">Use of the characteristics in rectification</td> <td style="text-align: right; padding: 5px;">1</td> </tr> </table> <div style="text-align: center; margin-top: 10px;">  </div>	(a) Processes involved in the formation of depletion region	2	(b) Circuit diagrams	1/2 + 1/2	V-I characteristics in forward biasing and reverse biasing	1/2 + 1/2	Use of the characteristics in rectification	1	<p>1</p>	<p>3</p>
(a) Processes involved in the formation of depletion region	2										
(b) Circuit diagrams	1/2 + 1/2										
V-I characteristics in forward biasing and reverse biasing	1/2 + 1/2										
Use of the characteristics in rectification	1										

Two processes involved during the formation of p-n junction are diffusion and drift . Due to the concentration gradient, across p and n sides of the junction , holes diffuse from p \rightarrow n , and electrons from n \rightarrow p . This movement of charge carriers leaves behind ionised acceptors on the p-side and donors on the n- side of the junction . This space charge region on either side of the junction , together , is known as depletion region.

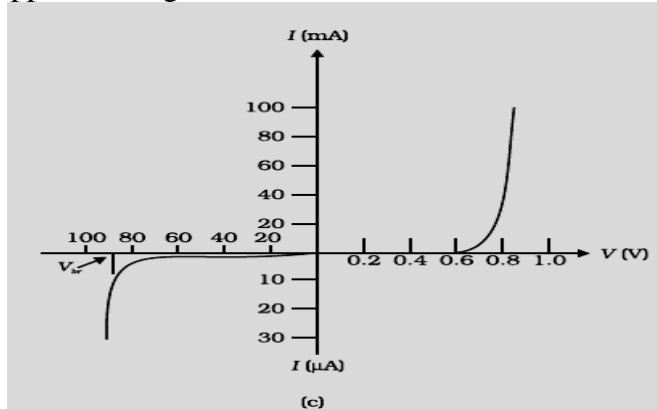
1

(b)



$\frac{1}{2} + \frac{1}{2}$

Using the circuit arrangements shown in fig (a) and fig (b) , we study the variation of current with applied voltage to obtain the V-I characteristics shown below.



$\frac{1}{2} + \frac{1}{2}$

From the V-I characteristics of a junction diode . it is clear that it allows the current to pass only when it is forward biased. So when an alternatively voltage is applied across the diode , current flows only during that part of the cycle when it is forward biased.

1

5

OR

(a) Differences between three segments of a transistor	$\frac{1}{2} + \frac{1}{2} + \frac{1}{2}$
(b) Transistor biasing in active state	$\frac{1}{2}$
(c) Circuit diagram of npn transistor in CE configuration for an amplifier and its brief description	$1\frac{1}{2} + 1$
Expression for the ac current gain	$\frac{1}{2}$

- (a) Emitter : It is of moderate size and heavily doped
 Base : It is very thin and lightly doped
 Collector : It is moderately doped and larger in size

$\frac{1}{2}$
 $\frac{1}{2}$
 $\frac{1}{2}$

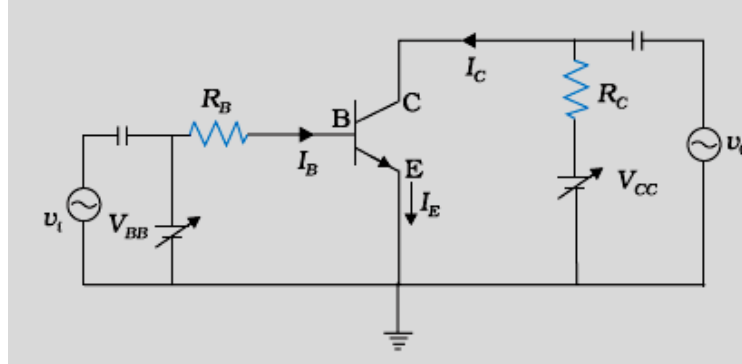
- (b) Transistor is said to be in active state when its emitter-base junction is (suitably) forward biased and base-collector junction is (suitably) reverse

$\frac{1}{2}$

biased.

[**Note** : In the active region, the emitter-base voltage lies between nearly 0.6 volt and 1.0 volt.]

(c)



When a small sinusoidal voltage is superposed on the dc base bias , the base current will have sinusoidal variation superimposed on the value of I_B
As a consequence , the collector current also will have sinusoidal variations , superimposed on the value of I_C , producing corresponding (amplified) changes in the value of V_0 .

$$\text{ac current gain } \beta_{ac} = \left(\frac{\Delta I_C}{\Delta I_B} \right)_{V_{CE}}$$

1½

1

½

5

29.

(a) (i) Reason	1
(ii) Obtaining expression for the resultant intensity	2
(b) Finding the intensity of light at a required point	2

(a) Light waves, originating from two independent monochromatic sources, will not have a constant phase difference. Therefore, these sources will not be coherent and, therefore , would not produce a sustained interference pattern.

$$\begin{aligned} \text{(b) (i) } y &= y_1 + y_2 \\ &= a \cos \omega t + a \cos(\omega t + \phi) \\ &= 2a \cos \frac{\phi}{2} \cdot \cos \left(\omega t + \frac{\phi}{2} \right) \end{aligned}$$

Amplitude of resultant displacement is $2a \cos \frac{\phi}{2}$

∴ Intensity ,

$$I = 4 a^2 \cos^2 \frac{\phi}{2}$$

Note : Accept ,if a student derives the expression

$$I = C [a_1^2 + a_2^2 + 2a_1 a_2 \cos \phi] \quad \text{where 'a' is the amplitude of the monochromatic light.}$$

(ii) A path difference of λ , corresponds to a phase difference of 2π

$$\therefore \text{ The intensity, } K = 4a^2 \Rightarrow a^2 = \frac{K}{4}$$

A path difference of $\frac{\lambda}{3}$, corresponds to a phase difference of $\frac{2\pi}{3}$

1

½

½

½

½

½

½

½

$$\therefore \text{Intensity} = 4 \times \frac{K}{4} \cdot \cos^2 \frac{2\pi}{3} = \frac{K}{4}$$

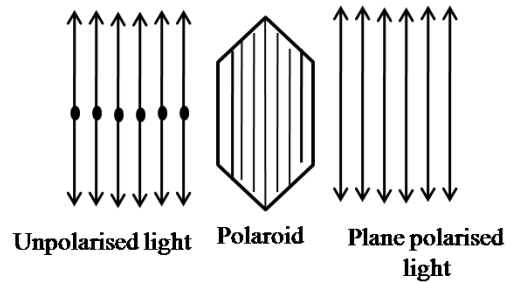
1/2

5

OR

- | | |
|--|---|
| (a) Demonstration of polarisation by a polaroid | 2 |
| (b) Showing polarisation by reflection at $\mu = \tan i_B$ | 3 |

(a)



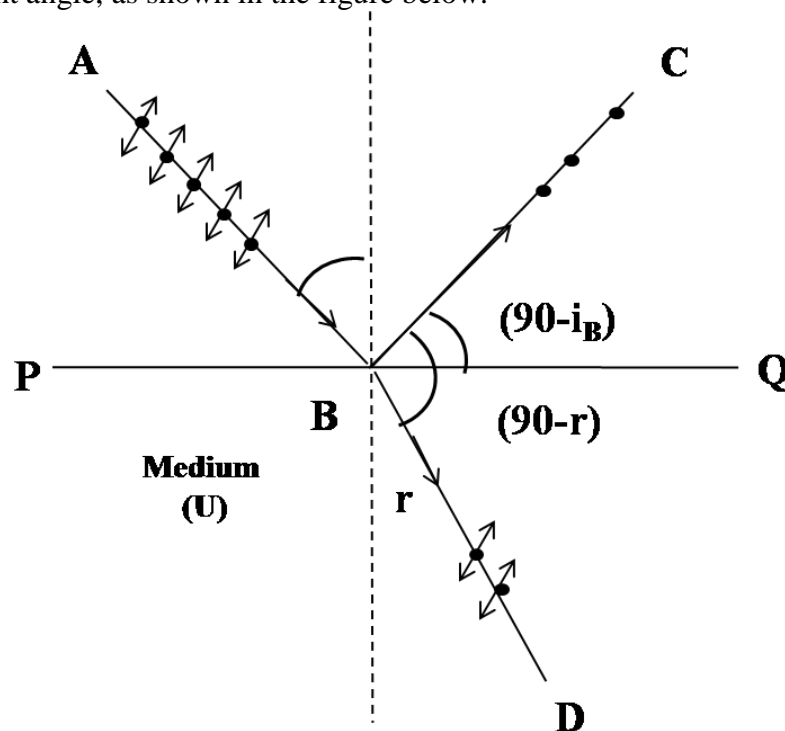
1

The components of electric vector associated with light wave, along the direction of aligned molecules of a polaroid, get absorbed. As a result after passing through it, the components perpendicular to the direction of aligned molecules will be obtained in the form of plane polarised light.

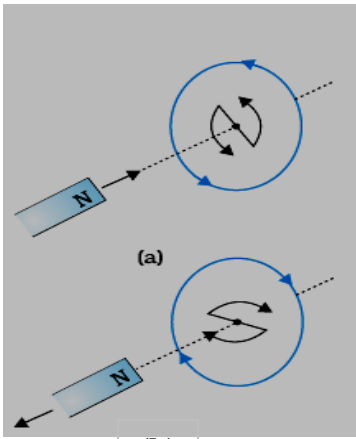
1

- (b) When unpolarised light is incident on the boundary between two transparent media, the reflected light is polarised, with electric vector perpendicular to the plane of incidence when the reflected and refracted light rays make a right angle, as shown in the figure below.

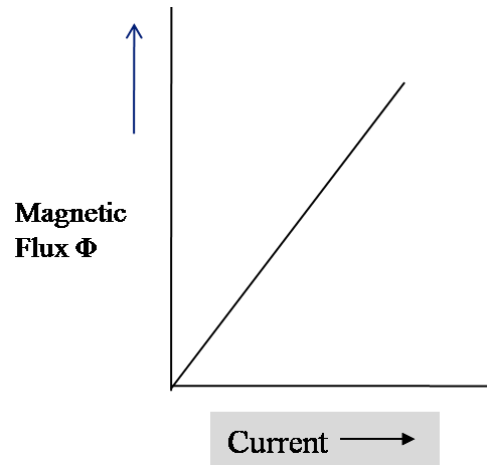
1/2



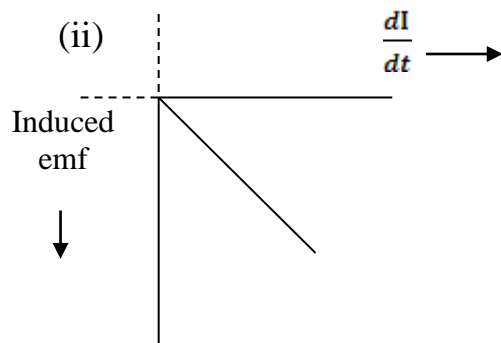
1

	<p>Since , $\angle CBQ + \angle QBD = 90^\circ$ $(90 - i_B) + (90 - r) = 90^\circ$ $i_B + r = 90^\circ$ $r = 90 - i_B$ Using Snell's law,</p> $\mu = \frac{\sin i_B}{\sin r}$ $= \frac{\sin i_B}{\sin(90 - i_B)}$ $= \frac{\sin i_B}{\cos i_B}$ $\mu = \tan i_B$	<p>1/2 1/2 1/2</p>	<p>5</p>										
<p>30.</p>	<table border="1" data-bbox="243 646 1221 913"> <tr> <td>(a) Description of an experiment/activity showing the polarity of emf induced</td> <td>2</td> </tr> <tr> <td>(b) Plots showing variation of</td> <td></td> </tr> <tr> <td> (i) Magnetic flux vs current</td> <td>1</td> </tr> <tr> <td> (ii) Induced emf vs dI/dt</td> <td>1</td> </tr> <tr> <td> (iii)Magnetic Potential energy vs current</td> <td>1</td> </tr> </table> <p>(a)</p>  <p>(b)</p> <p>When a bar magnet is brought close to the coil (fig a), the approaching North Pole of the bar magnet increases the magnetic flux linked to it. This produces an induced emf which produces (or tends to produce, if the coil is open) an induced current in the anti-clockwise sense. The face of the coil, facing the approaching magnet, then has the same polarity as that of the approaching pole of the magnet. The induced current, therefore, is seen to oppose the change of magnetic flux that produces it.</p> <p>[Note: Give full credit to the candidate who explains this activity by considering the motion of the magnet away from the coil(Fig b) and says that the induced current is in clockwise sense.]</p>	(a) Description of an experiment/activity showing the polarity of emf induced	2	(b) Plots showing variation of		(i) Magnetic flux vs current	1	(ii) Induced emf vs dI/dt	1	(iii)Magnetic Potential energy vs current	1	<p>1 1</p>	
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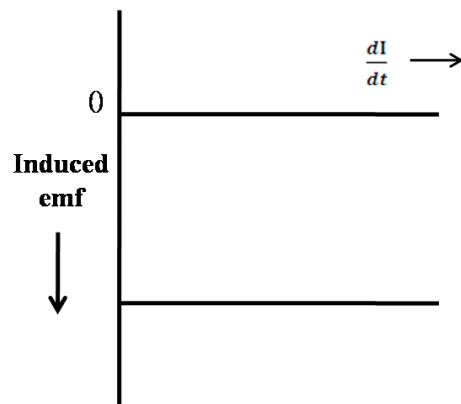
(b) (i) Magnetic flux versus current



1



Alternatively ,

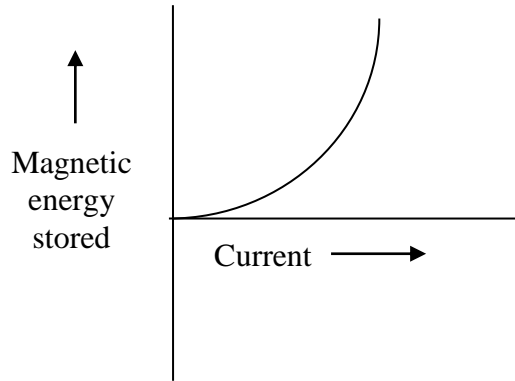


1

When I is increasing at constant value.

[**Note :** If the student draws induced emf vs $\frac{dI}{dt}$ graph of any shape, while keeping induced emf -ve , award this 1 mark.]

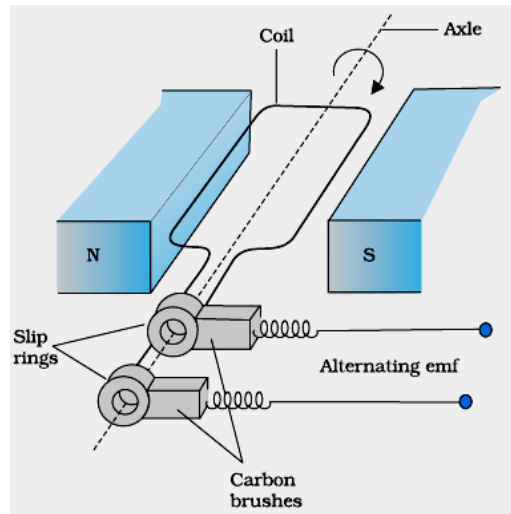
(iii) Magnetic energy stored



[Note: If a student writes only the mathematical formulae for these cases, award ½ mark for each case]

OR

(a) Schematic sketch of ac generator	1½
Working principle	1
Plot of variation of (i) Magnetic flux and (ii) alternating emf vs time	1+1
(b) Need of choke coil	½



It works on the process of electromagnetic induction, i.e. when a coil rotates continuously in a magnetic field, the effective area of the coil, linked (normally) with the magnetic field lines, changes continuously with time. This variation of magnetic flux with time results in the production of an (alternating) emf in the coil.

1

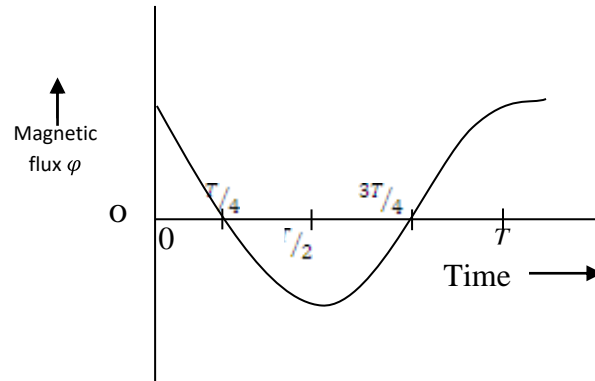
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1½

1

(1) Magnetic flux versus time

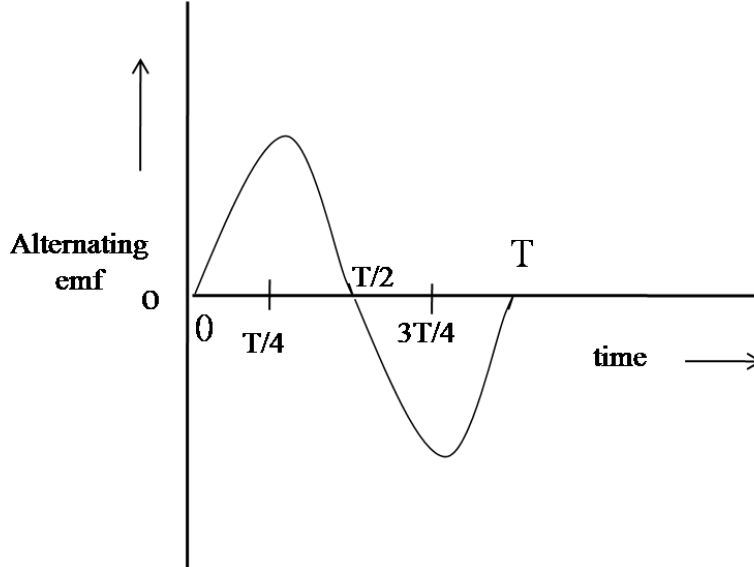
$$\phi = NBA \cos \omega t$$



1

(2) Alternating emf versus time

$$e = NAB\omega \sin \omega t$$
$$= e_0 \sin \omega t$$



1

[Note : Give credit of 1/2 mark for each case for writing the mathematical expressions without plotting the graphs.]

(b)A choke coil reduces the volatge across the fluorescent tube without wastage of power.

[Note : Award these 1/2 marks if the student gives any other significant reason.]

1/2

5